

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

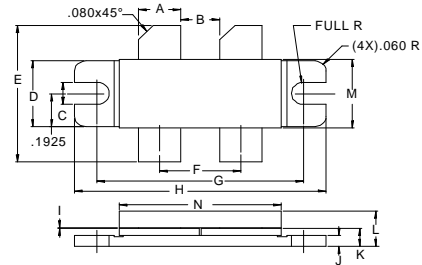
The **ASI CBSL150** is Designed for 900 MHz Class AB Cellular Base Station Amplifiers.

FEATURES:

- **Internal** Input/Output Matching
- $P_G = 9.0$ dB Typ. at 150 W/ 900 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	25 A
V_{CEO}	28 V
V_{CES}	60 V
V_{EBO}	3.5 V
P_{DISS}	300 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.6 °C/W

PACKAGE STYLE .400 BAL FLG (C)


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.210 / 5.33	
C	.120 / 3.05	.130 / 3.30
D	.380 / 9.65	.390 / 9.91
E	.780 / 19.81	.820 / 20.83
F	.435 / 11.05	
G	1.090 / 27.69	
H	1.335 / 33.91	1.345 / 34.16
I	.003 / 0.08	.007 / 0.18
J	.060 / 1.52	.070 / 1.78
K	.082 / 2.08	.100 / 2.54
L	.205 / 5.21	
M	.395 / 10.03	.407 / 10.34
N	.850 / 21.59	.870 / 22.10

ORDER CODE: ASI10586
CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA	26			V
BV_{CER}	$I_C = 100$ mA $R_{BE} = 200 \Omega$	35			V
BV_{CES}	$I_C = 50$ mA	60			V
BV_{EBO}	$I_E = 10$ mA	3.5			V
I_{CES}	$V_{CE} = 30$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	30	45	120	---
P_G	$V_{CC} = 26$ V $P_{OUT} = 150$ W $I_{CQ} = 2 \times 150$ mA	8.0			dB
IMD	$f = 960$ MHz			-28	dBc
η_C		35			%
ψ	VSWR = 5:1 at all phase angles	No Degradation in Output Power			